**74LVC38A** Quad 2-input NAND gate; open-drain Rev. 4 – 4 November 2011

**Product data sheet** 

### 1. General description

The 74LVC38A provides four 2-input NAND functions. The outputs are open-drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

### 2. Features and benefits

- 5 V tolerant inputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 5.5 V
- CMOS low power consumption
- Direct interface with TTL levels
- Open-drain outputs
- Complies with JEDEC standard:
  - ◆ JESD8-7A (1.65 V to 1.95 V
  - JESD8-5A (2.3 V to 2.7 V
  - ◆ JESD8-C/JESD36 (2.7 V to 3.6 V
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115B exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

## 3. Ordering information

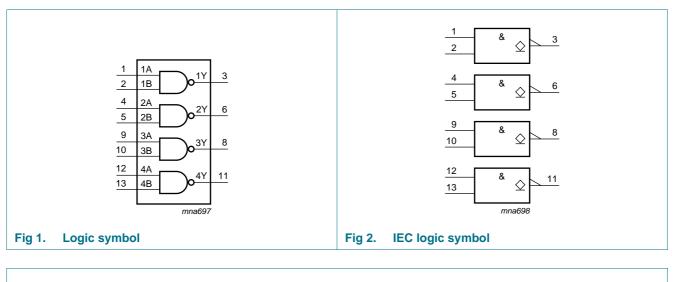
#### Table 1. Ordering information

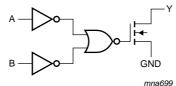
Type number	Package							
	Temperature range	Name	Description	Version				
74LVC38AD	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1				
74LVC38ADB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1				
74LVC38APW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1				
74LVC38ABQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1				



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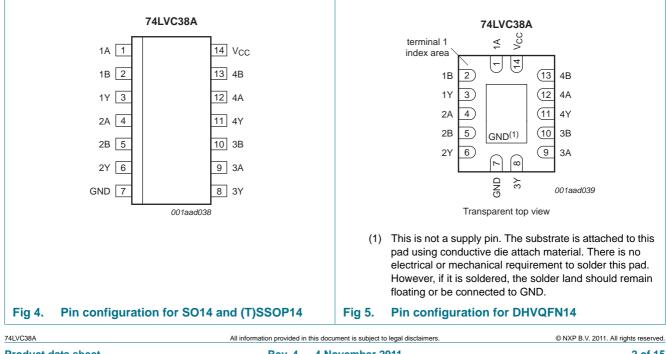
#### **Functional diagram** 4.







#### **Pinning information** 5.



#### 5.1 **Pinning**

## 5.2 Pin description

Table 2. Pin des	scription	
Symbol	Pin	Description
1A, 2A, 3A, 4A	1, 4, 9, 12	data input
1B, 2B, 3B, 4B	2, 5, 10, 13	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

#### Table 3.Function selection[1]

Input		Output
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state

## 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0	-50	-	mA
Vo	output voltage	active mode	[2] -0.5	+6.5	V
		high-impedance mode	[2] -0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	50	mA
I <sub>CC</sub>	supply current		-	100	mA
I <sub>GND</sub>	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[3] _	500	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] For SO14 packages: above 70 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K. For (T)SSOP14 packages: above 60 °C the value of P<sub>tot</sub> derates linearly with 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P<sub>tot</sub> derates linearly with 4.5 mW/K.

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## 8. Recommended operating conditions

Table 5.	Recommended operating co	onditions				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		1.65	-	5.5	V
		functional	1.2	-	-	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	active mode	0	-	V <sub>CC</sub>	V
		high-impedance mode	0	-	5.5	V
T <sub>amb</sub>	ambient temperature	in free air	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall	$V_{CC}$ = 1.65 V to 2.7 V	0	-	20	ns/V
	rate	V <sub>CC</sub> = 2.7 V to 3.6 V	0	-	10	ns/V

## 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C to	–40 °C to +125 °C		
			Min	Typ[1]	Max	Min	Max		
VIH	HIGH-level	V <sub>CC</sub> = 1.2 V	1.08	-	-	1.08	-	V	
	input voltage	$V_{CC}$ = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	$0.65 \times V_{CC}$	-	V	
		$V_{CC}$ = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V	
		$V_{CC}$ = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V	
		$V_{CC}$ = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	$0.7\times V_{CC}$	-	V	
V <sub>IL</sub>	LOW-level input	V <sub>CC</sub> = 1.2 V	-	-	0.12	-	0.12	V	
	voltage	$V_{CC}$ = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	-	$0.35 \times V_{CC}$	V	
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V	
		$V_{CC}$ = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V	
		$V_{CC}$ = 4.5 V to 5.5 V	-	-	$0.30 \times V_{CC}$	-	$0.30\times V_{CC}$	V	
V <sub>OL</sub>	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$							
	output voltage	$I_{O}$ = 100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.20	-	0.3	V	
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	-	0.65	V	
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.6	-	0.8	V	
		$I_{O}$ = 12 mA; $V_{CC}$ = 2.7 V	-	-	0.4	-	0.6	V	
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.8	V	
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	-	0.8	V	
lı	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V$	-	±0.1	±5	-	±20	μA	
I <sub>OZ</sub>	OFF-state output current		-	0.1	±5	-	±20	μΑ	
I <sub>OFF</sub>	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	±0.1	±10	-	±20	μΑ	

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Symbol	Parameter	ter Conditions	-40	–40 °C to +85 °C			o +125 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
I <sub>CC</sub>	supply current		-	0.1	10	-	40	μA
$\Delta I_{CC}$	additional supply current	per input pin; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.7 V to 5.5 V	-	5	500	-	5000	μΑ
CI	input capacitance	$V_{CC} = 0 V$ to 5.5 V; V <sub>I</sub> = GND to V <sub>CC</sub>	-	4.0	-	-	-	pF

#### Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

[1] All typical values are measured at V<sub>CC</sub> = 3.3 V (unless stated otherwise) and T<sub>amb</sub> = 25 °C.

## **10.** Dynamic characteristics

#### Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions	-	40 °C to +8	5 ℃	-40 °C t	o +125 °C	Unit
			Mir	n Typ <mark>[1]</mark>	Max	Min	Max	
t <sub>PZL</sub>	t <sub>PZL</sub> OFF-state to LOW propagation delay	nA, nB to nY; see Figure 6				1	1	
		V <sub>CC</sub> = 1.2 V	-	5.7	-	-	-	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.0	2.6	6.0	1.0	6.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V	0.5	1.8	3.3	0.5	3.8	ns
		$V_{CC} = 2.7 V$	0.5	1.7	2.9	0.5	4.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.5	1.8	3.0	0.5	4.0	ns
t <sub>PLZ</sub>	LOW to OFF-state	nA, nB to nY; see Figure 6						
	propagation delay	V <sub>CC</sub> = 1.2 V	-	5.7	-	-	-	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.0	2.7	6.0	1.0	6.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V	0.5	1.5	3.3	0.5	3.8	ns
		$V_{CC} = 2.7 V$	1.0	2.6	3.8	1.0	5.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.3	3.6	1.0	4.5	ns
t <sub>sk(o)</sub>	output skew time		[2] _	-	1.0	-	1.5	ns

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Symbol	Parameter	meter Conditions		–40 °C to +85 °C			–40 °C to	–40 °C to +125 °C	
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
C <sub>PD</sub> power dissipation capacitance	per gate; $V_I = GND$ to $V_{CC}$	[3]							
	$V_{CC}$ = 1.65 V to 1.95 V		-	6.2	-	-	-	pF	
		$V_{CC}$ = 2.3 V to 2.7 V		-	9.7	-	-	-	pF
		$V_{CC}$ = 3.0 V to 3.6 V		-	12.9	-	-	-	pF

#### Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V). For test circuit see <u>Figure 7</u>.

[1] Typical values are measured at  $T_{amb}$  = 25 °C and  $V_{CC}$  = 1.2 V, 1.8 V, 2.5 V, 2.7 V, and 3.3 V respectively.

[2] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;  $f_o$  = output frequency in MHz

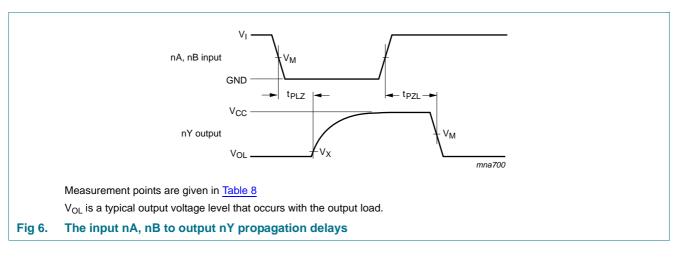
 $C_L$  = output load capacitance in pF

 $V_{CC}$  = supply voltage in Volts

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs

## **11. AC waveforms**



#### Table 8. Measurement points

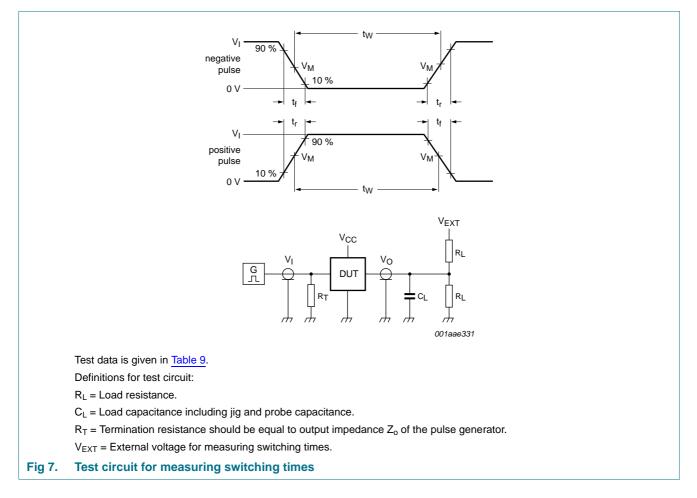
Supply voltage	Input	Output
V <sub>cc</sub>	V <sub>M</sub>	V <sub>X</sub>
<2.7 V	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.15 V
≥2.7 V to 3.6 V	1.5 V	V <sub>OL</sub> + 0.3 V

74LVC38A Product data sheet

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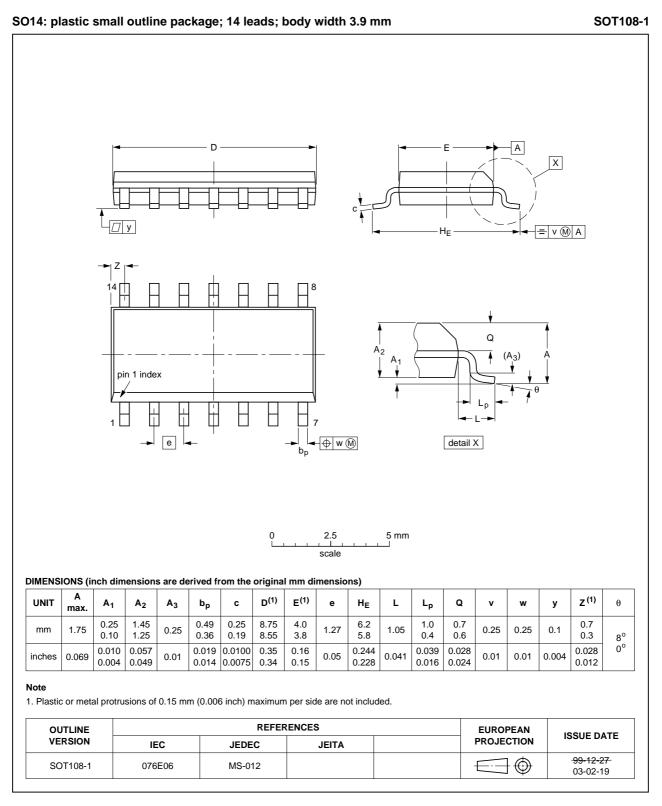


#### Table 9. Test data

Supply voltage	Input	Input			V <sub>EXT</sub>	V <sub>EXT</sub>		
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PLZ</sub> , t <sub>PZL</sub>		
1.2 V	V <sub>CC</sub>	$\leq$ 2 ns	30 pF	1 kΩ	open	$2 \times V_{CC}$		
1.65 V to 1.95 V	V <sub>CC</sub>	$\leq$ 2 ns	30 pF	1 kΩ	open	$2 \times V_{CC}$		
2.3 V to 2.7 V	V <sub>CC</sub>	$\leq$ 2 ns	30 pF	500 Ω	open	$2 \times V_{CC}$		
2.7 V	2.7 V	$\leq$ 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$		
3.0 V to 3.6 V	2.7 V	$\leq$ 2.5 ns	50 pF	500 Ω	open	$2 \times V_{CC}$		

Quad 2-input NAND gate; open-drain

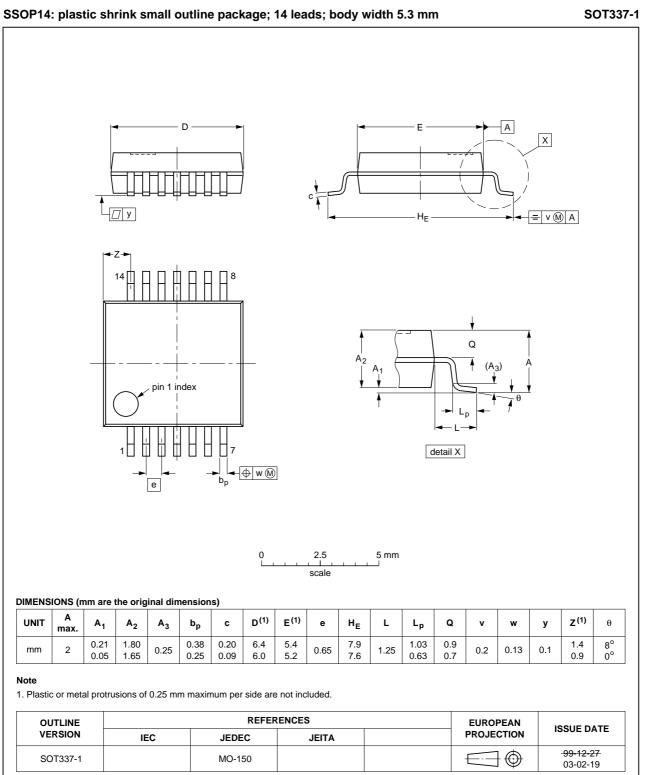
### 12. Package outline



#### Fig 8. Package outline SOT108-1 (SO14)

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#### Fig 9. Package outline SOT337-1 (SSOP14)

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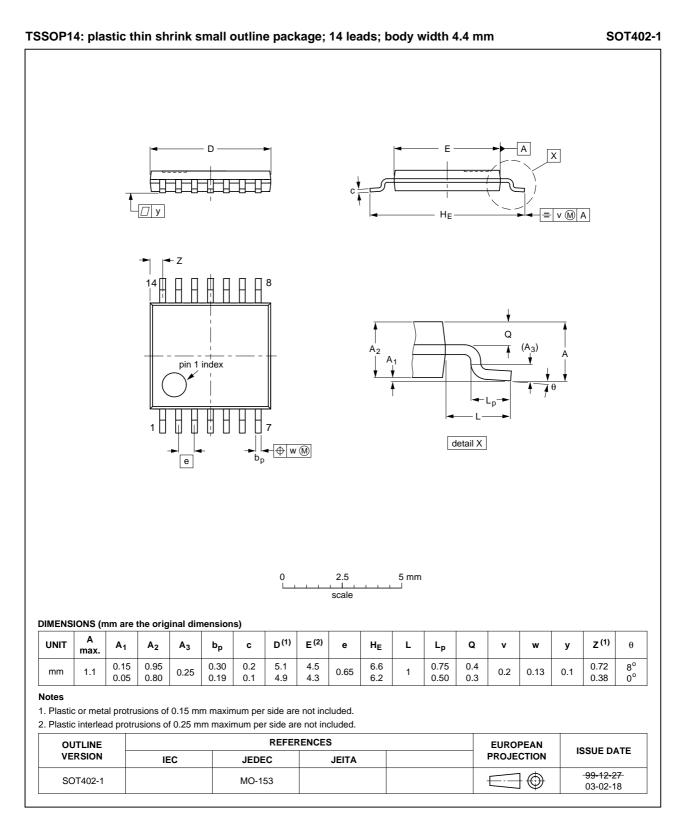
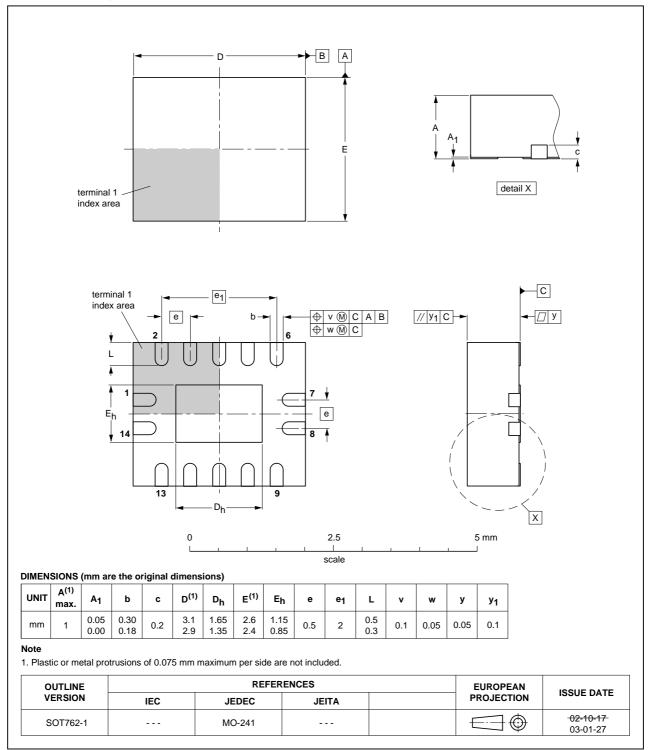


Fig 10. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

#### Fig 11. Package outline SOT762-1 (DHVQFN14)

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### Quad 2-input NAND gate; open-drain

## **13. Abbreviations**

Table 10.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 14. Revision history

Table 11. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74LVC38A v.4	20111104	Product data sheet	-	74LVC38A v.3	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>				
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
	<ul> <li><u>Table 4</u>, <u>Table 5</u>, <u>Table 6</u>, <u>Table 7</u> and <u>Table 8</u>: values added for lower voltage ranges.</li> </ul>				
74LVC38A v.3	20040322	Product specification	-	74LVC38A v.2	
74LVC38A v.2	20040310	Product specification	-	74LVC38A v.1	
74LVC38A v.1	20020408	-	-	-	

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### 15.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Rev. 4 — 4 November 2011

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